

DEPFET Active Pixel Sensors for the ILC

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for the DEPFET Collaboration (<u>www.depfet.org</u>)





- fully depleted sensitive volume, charge collection by drift
- internal amplification \rightarrow q-I conversion: 0.4 nA/e, scales with gate length and bias current
- Charge collection in "off" state, read out on demand





- select row with external gate, read current, clear DEPFET, read current again → the difference is the signal
- Low power consumption
- two different auxiliary ASICs needed
- limited frame rate
- cap. load at the f/e adds noise

drain 🕁

0 suppression

V_{CLEAR OFF}

V_{CLEAR-Control}



• However, we need (almost..) complete clear \rightarrow Hans-Günther's talk..

ILC VXD baseline design





Just as a starting point for the R&D!

- 5 layer, old TESLA layout
- 10 and 25 cm long ladders read out at the ends
- 24 micron pixel
- design goal 0.1% X₀ per layer in the sens. region

Strategy to cope with the background:

- read ~20 times per train
- store data on ladder
- transfer the data off ladder in the train pause
 → row rate of 40 MHz
- read two rows in parallel, doubles # r/o channels but:

→ row rate 20 MHz 🙂



Work sharing in the collaboration



	DEPFET/Ladder	Auxiliary ASICs	System	System Tests and
	Sim. and Irrad.	Development	Development	Test Beams
Aachen			Х	
Bonn		Х	Х	Х
Karlsruhe	Х			
Mannheim		Х	Х	Х
Munich	Х			Х
Prague			Х	Х
Valencia			Х	Х

The next 120 minutes

0	Hans-Guenther:	DEPFET Design and Test, Radiation Tolerance, Ladder Concept
0	Ivan:	ASICs: Steering and f/e ASIC
0	Carlos:	Test of the Prototype System
0	Ariane:	ILC VXD Simulation
		Summary and Future Plans